

ABSTRACT

There is provided a tungsten sputtering target that can provide a film deposition rate with less fluctuation over the target life. A tungsten sputtering target, wherein an area ratio of crystal grains having any of {100}, {110} and {111} planes oriented to a sputtering surface is 30% or less for any of the orientation planes, and an area ratio in total of crystal grains having orientation planes oriented to the sputtering surface other than {100}, {110} and {111} planes is 46% or more, the area ratio being obtained by an analysis of a cross section perpendicular to the sputtering surface with an inverse pole figure mapping using electron backscatter diffraction,